

REMARKS

This Application is a Continued Prosecution Application (CPA) of Application No. 09/429,530. Claims 11 to 20, 25 to 27, 30 to 32 and 45 to 54 are in the application, of which Claims 11 and 45 are the independent claims. Claims 21 to 24, 28, 29 and 33 to 44 have been cancelled without prejudice or disclaimer of the subject matter presented therein, and without conceding the correctness of the rejection. Claims 11, 12, 25 and 27 have been amended and new Claims 45 to 54 have been added. Favorable review and passage to issue are respectfully requested.

Applicant's undersigned attorney may be reached in our Costa Mesa, California office at (714) 540-8700. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,

  
Attorney for Applicant

Registration No. 32622

FITZPATRICK, CELLA, HARPER & SCINTO  
30 Rockefeller Plaza  
New York, New York 10112-2200  
Facsimile: (212) 218-2200

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APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE TO CLAIMS

11. (Amended) A fabrication method of a semiconductor device comprising:

[(a) forming, on a substrate, an insulating film at which at least one of a wiring pattern or a contact pattern is formed;

(b) forming a metal in the at least one of the wiring pattern or the contact pattern;

(c) polishing a surface of the metal; and]

a first step of forming a first insulating film on a substrate, said substrate having a semiconductor region;

a second step of forming a second insulating film on the substrate, said second insulating film being of a different material than the first insulating film and serving as a polishing stopper;

a third step of forming by an etching process an opening in the second insulating film, wherein a part of the second insulating film remains within said opening;

a fourth step of forming a metal film on the second insulating film and the opening, wherein the metal film has a polishing rate greater than that of the second insulating film;

a fifth step of polishing the metal film to expose a surface of the second insulating film etched in the third step and to form a flat plane comprising the exposed surface of the second insulating film and a polished surface of the metal film; and

a sixth step of

[(d)] washing the polished surface of the metal film by (i) conducting an ultrasonic wave washing of said polished surface employing a washing liquid; and (ii) conducting a physical washing of said polished surface after the ultrasonic wave washing.

12. (Amended) A fabrication method of a semiconductor device according to claim 11, wherein said polishing step [(c)] is conducted employing chemical mechanical polishing.

25. (Amended) A fabrication method according to claim 11, wherein said metal film is Al, Cu, Au, Cr, Mo, Pt, Ti or an alloy thereof.

27. (Unamended From Previous Version) A fabrication method according to claim 11, including forming a barrier metal prior to forming the metal film.